



## Description

The XPX80N021LL uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.

$V_{DS} = 80V, I_D = 200A$

$R_{DS(ON)} = 2.1m\Omega$  (typ) @  $V_{GS} = 10V$

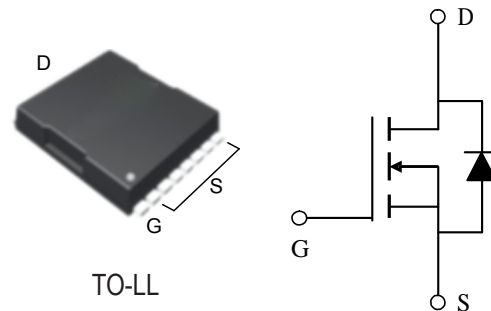
$R_{DS(ON)} = 2.6m\Omega$  (typ) @  $V_{GS} = 4.5V$

## General Features

- High density cell design for ultra low  $R_{DS(on)}$
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high  $E_{AS}$
- Excellent package for good heat dissipation

## Application

- PWM
- Load Switching



## Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
XPX80N021LL	XPX80N021LL	TO-LL	-	-	2000

## Absolute Maximum Ratings ( $T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	80	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	200	A
Drain Current-Continuous( $T_C = 100^\circ C$ )	$I_D(100^\circ C)$	120	A
Pulsed Drain Current	$I_{DM}$	610	A
Maximum Power Dissipation	$P_D$	231	W
Derating factor		1.85	W/ $^\circ C$
Single pulse avalanche energy (Note 5)	$E_{AS}$	552	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 175	$^\circ C$
Thermal Resistance, Junction-to-Case(Note 2)	$R_{\theta JC}$	0.68	$^\circ C/W$

**Electrical Characteristics** ( $T_A = 25^\circ\text{C}$  unless otherwise noted)

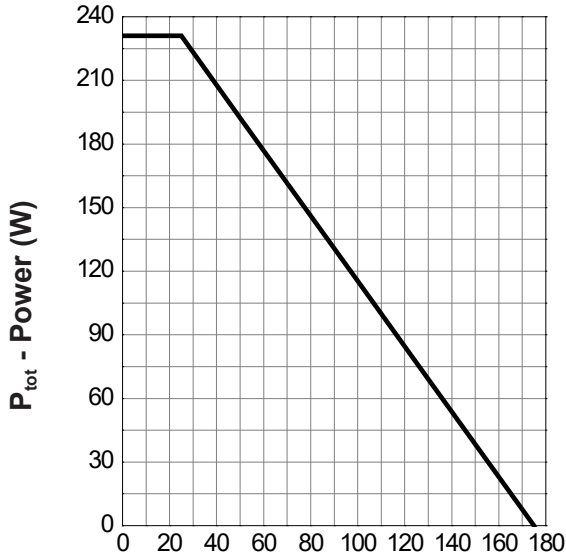
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static Characteristics</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_{DS}=250\mu A$	80	-	-	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=64V, V_{GS}=0V$	-	-	1	$\mu A$
		$T_J=85^\circ C$	-	-	30	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_{DS}=250\mu A$	2	3	4	V
$I_{GSS}$	Gate Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA
$R_{DS(ON)}^c$	Drain-Source On-state Resistance	$V_{GS}=10V, I_{DS}=80A$	-	2.1	2.9	m $\Omega$
<b>Diode Characteristics</b>						
$V_{SD}^c$	Diode Forward Voltage	$I_{SD}=40A, V_{GS}=0V$	-	0.8	1.1	V
$t_{rr}^d$	Reverse Recovery Time	$I_{SD}=80A, di_{SD}/dt=100A/\mu s$	-	65	-	ns
$Q_{rr}^d$	Reverse Recovery Charge		-	113	-	nC
<b>Dynamic Characteristics<sup>d</sup></b>						
$R_G$	Gate Resistance	$V_{GS}=0V, V_{DS}=0V, F=1MHz$	-	1	-	$\Omega$
$C_{iss}$	Input Capacitance	$V_{GS}=0V,$ $V_{DS}=50V,$ Frequency=1.0MHz	-	5500	7150	pF
$C_{oss}$	Output Capacitance		-	873	-	
$C_{riss}$	Reverse Transfer Capacitance		-	117	-	
$t_{d(ON)}$	Turn-on Delay Time	$V_{DD}=30V, R_L=30\Omega,$ $I_{DS}=1A, V_{GEN}=10V,$ $R_G=6\Omega$	-	34	61	ns
$t_r$	Turn-on Rise Time		-	15	28	
$t_{d(OFF)}$	Turn-off Delay Time		-	81	145	
$t_f$	Turn-off Fall Time		-	156	280	
<b>Gate Charge Characteristics<sup>d</sup></b>						
$Q_g$	Total Gate Charge	$V_{DS}=50V, V_{GS}=10V,$ $I_{DS}=80A$	-	82	115	nC
$Q_{gs}$	Gate-Source Charge		-	30	-	
$Q_{gd}$	Gate-Drain Charge		-	16	-	

Note c : Pulse test ; pulse width $\leq 300\mu s$ , duty cycle $\leq 2\%$ .

Note d : Guaranteed by design, not subject to production testing.

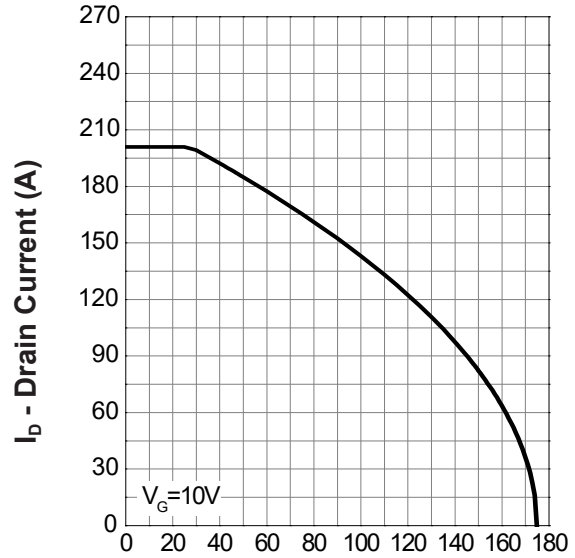
### Typical Operating Characteristics

**Power Dissipation**



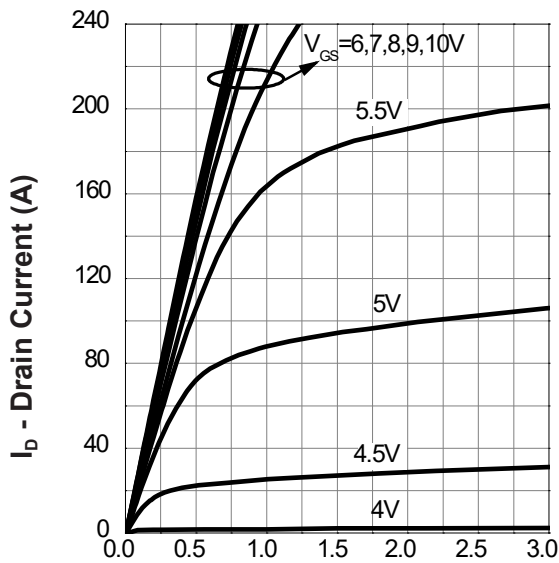
T<sub>c</sub> - Case Temperature (°C)

**Drain Current**



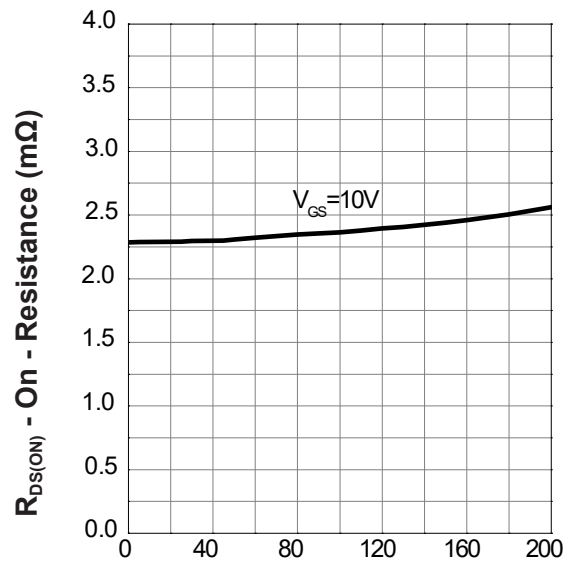
T<sub>c</sub> - Case Temperature (°C)

**Output Characteristics**



V<sub>DS</sub> - Drain - Source Voltage (V)

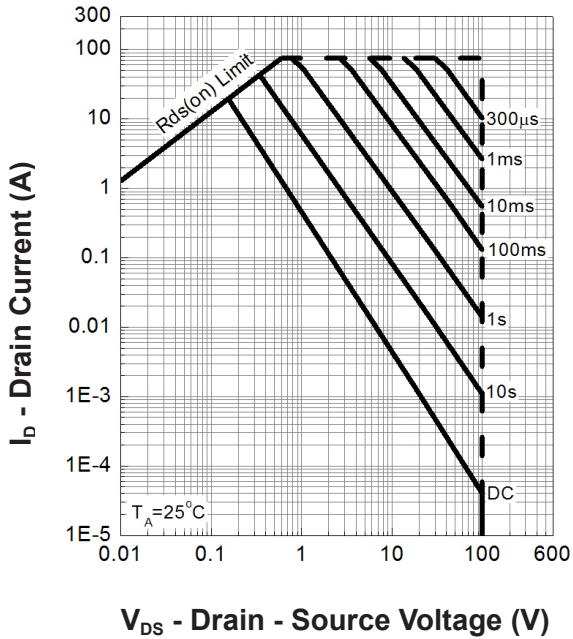
**Drain-Source On Resistance**



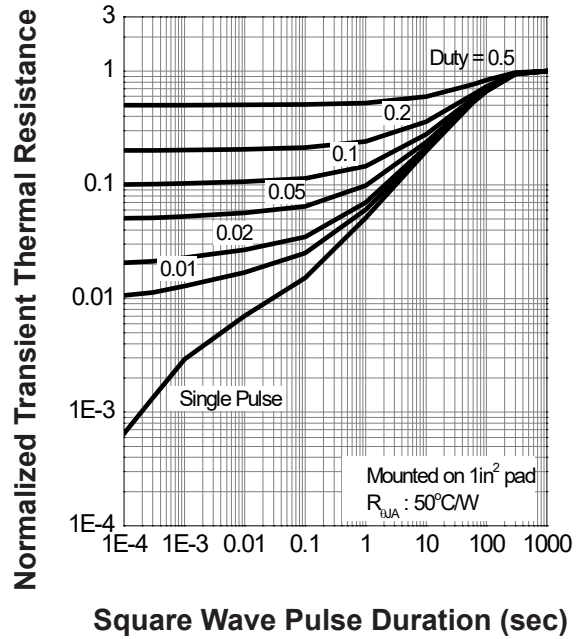
I<sub>b</sub> - Drain Current (A)

Typical Operating Characteristics(Cont.)

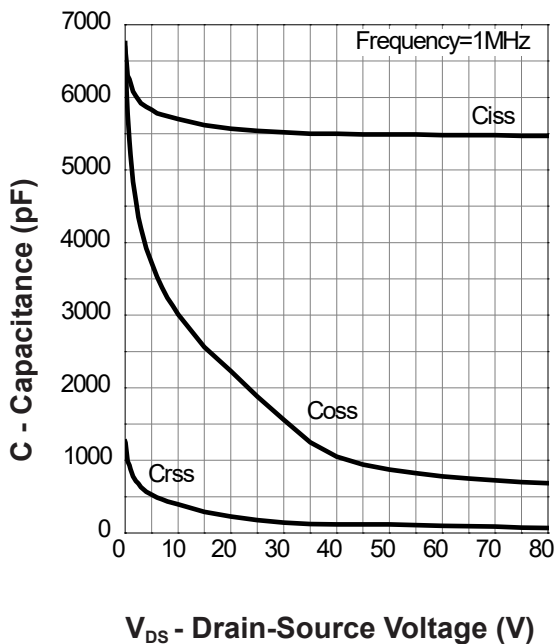
Safe Operation Area



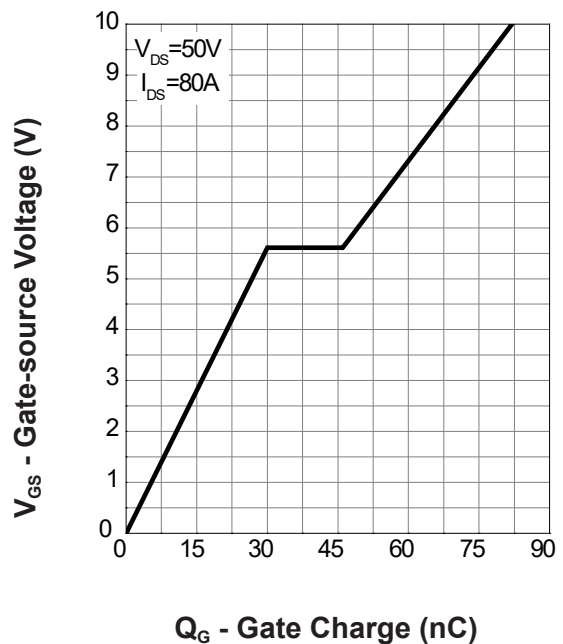
Thermal Transient Impedance



Capacitance

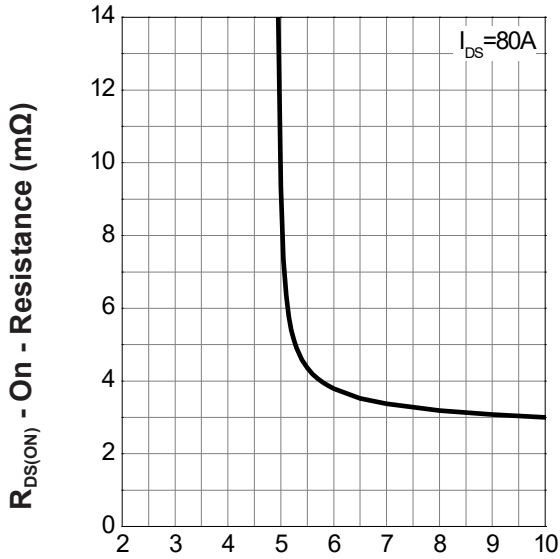


Gate Charge



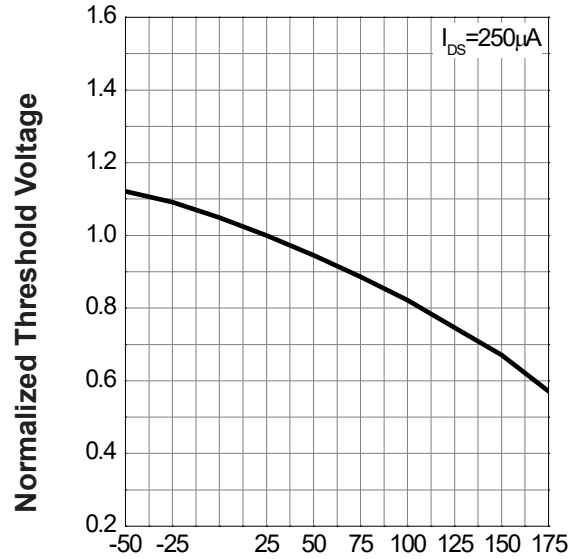
80V N-Channel Enhancement Mode MOSFET

Gate-Source On Resistance



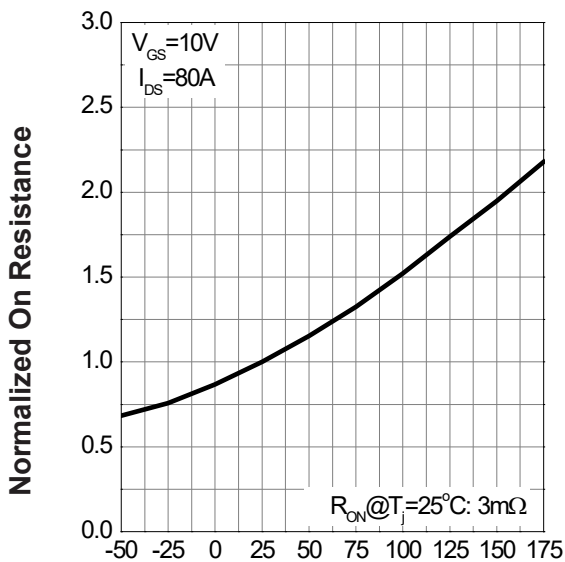
V<sub>GS</sub> - Gate - Source Voltage (V)

Gate Threshold Voltage



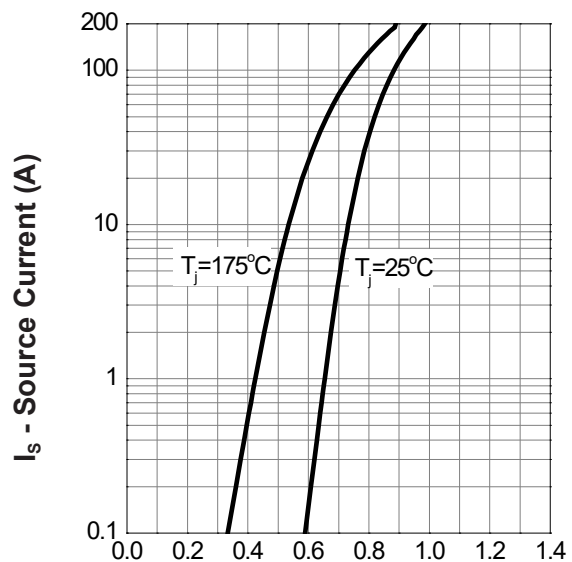
T<sub>J</sub> - Junction Temperature (°C)

Drain-Source On Resistance



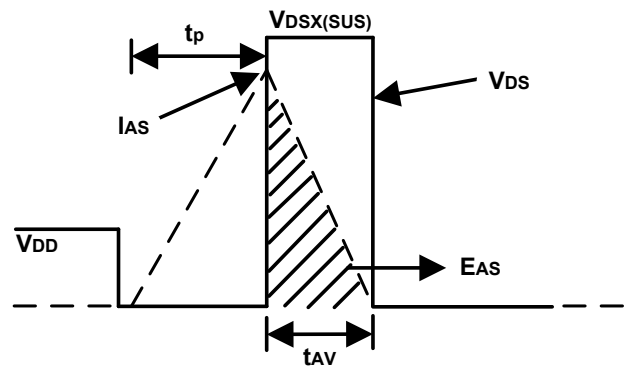
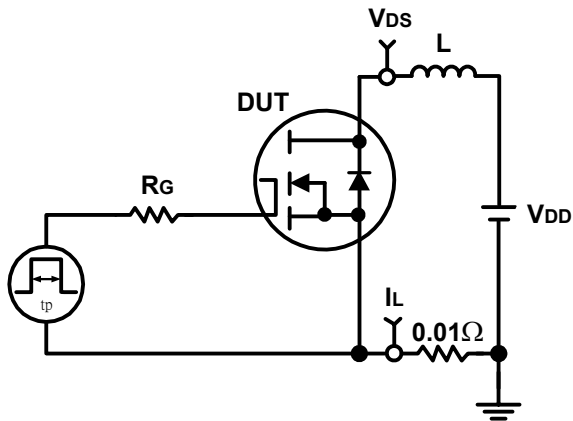
T<sub>J</sub> - Junction Temperature (°C)

Source-Drain Diode Forward

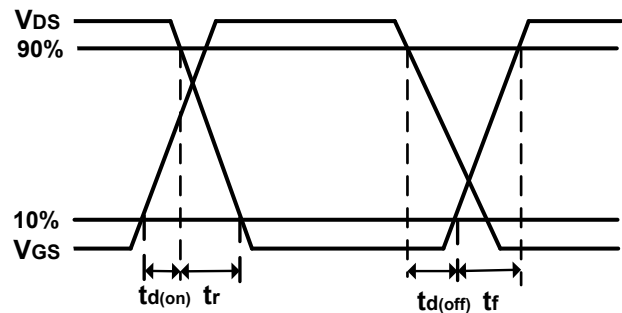
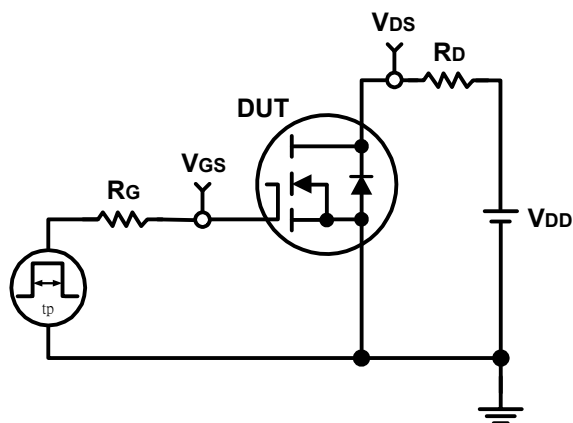


V<sub>SD</sub> - Source - Drain Voltage (V)

### Avalanche Test Circuit and Waveforms

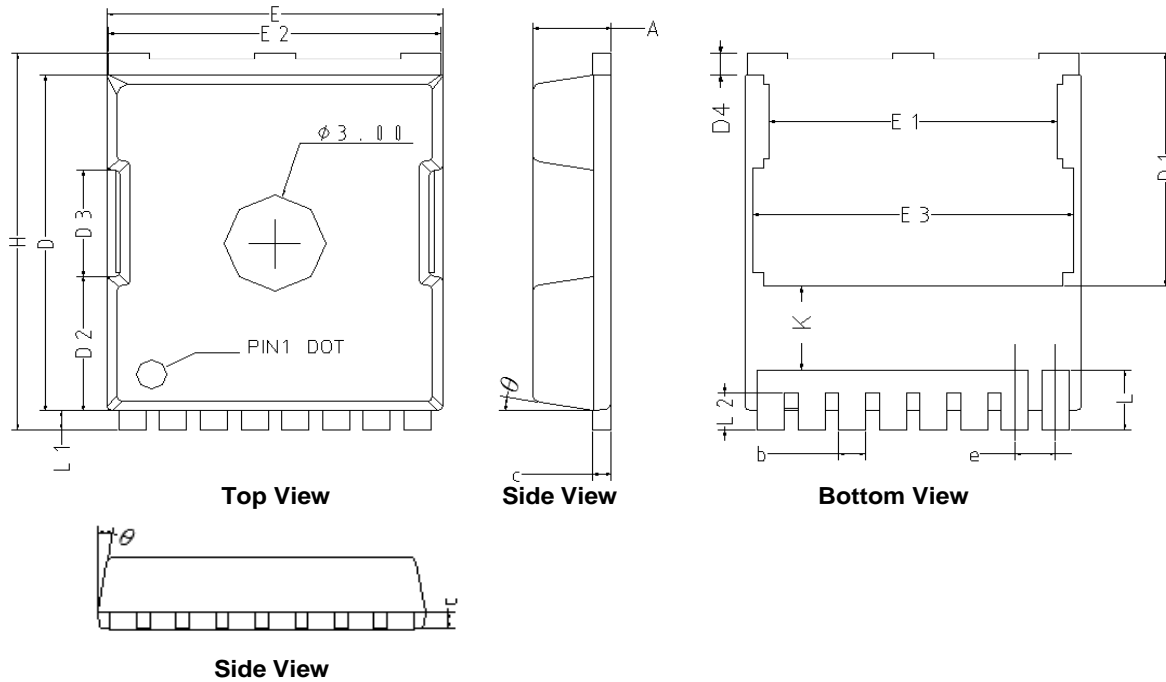


### Switching Time Test Circuit and Waveforms



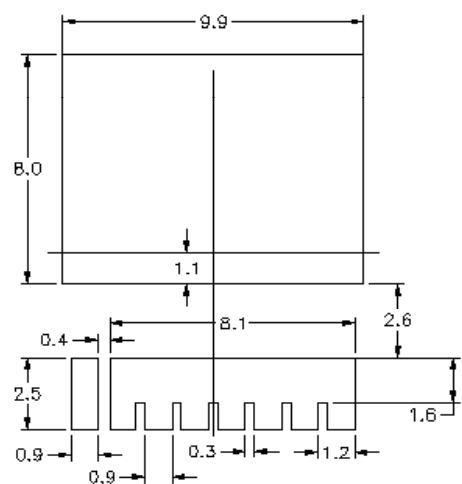
### Package Information

### TOLL



SYMBOLS	TO-LL			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	2.20	2.40	0.087	0.094
b	0.70	0.90	0.028	0.035
c	0.40	0.60	0.016	0.024
D	10.23	10.63	0.403	0.419
D1	7.05	7.45	0.278	0.293
D2	3.98	4.38	0.157	0.172
D3	3.10	3.50	0.122	0.138
D4	0.50	0.90	0.020	0.035
E	9.70	10.10	0.382	0.398
E1	8.30	8.70	0.327	0.343
E2	9.60	10.00	0.378	0.394
E3	9.26	9.66	0.365	0.380
H	11.53	11.93	0.454	0.470
e	1.2 BSC		0.0472 BSC	
K	2.43	2.83	0.096	0.111
L	1.65	2.05	0.065	0.081
L1	0.40	0.80	0.016	0.031
L2	0.95	1.35	0.037	0.053
$\theta$	6°	10°	6°	10°

### RECOMMENDED LAND PATTERN



UNIT: mm

80V N-Channel Enhancement Mode MOSFET

Flow (wave) soldering (solder dipping)

Product	Peak Temperature	Dipping Time
Pb device	245°C ±5°C	5sec ±1 sec
Pb-Free device	260°C +0/-5°C	5sec ±1 sec



This integrated circuit can be damaged by ESD. UniverChip Corporation recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedure can cause damage. ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

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